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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLN. OF: ASPAR et al.
SERIAL NO.: 10/784,601
FILED: February 23, 2004
FOR: A Method for Producing a Thin Layer of Semiconductor Material
GROUP: 2812
DOCKET: BREV 12370 CON4

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, it is respectfully requested that this Supplemental Information Disclosure Statement be entered and that the document listed on the attached Form PTO-1449 be considered by the Examiner and made of record.

Foreign Patent Document

SU 1282757, "A Method For Producing Thin Silicon Wafers"
Publication Date: June 27, 2000
Filing date: December 30, 1983
USSR Inventor's Certificate Specification No. 659061

The applicants are enclosing Form PTO-1449 along with a copy of the cited reference. A certified English translation of the cited reference and a copy of the bibliographic data maintained by the Russian Institute of Intellectual Property are included herewith.

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The applicants respectfully request the Examiner's consideration of the above reference and entry thereof into the record of this application. Based on the information available to the applicants, it is the applicants' belief that the cited reference was first published on June 27, 2000. As such, the applicants assert that the cited reference is not prior art to the applicants' patent application.

Although the cited reference is not prior art, because it was published after the May 14, 1997 U.S. priority filing date of the applicants' original patent application, the reference nevertheless shows the level of skill in the art as of the priority filing date of the above-referenced patent application. The reference discloses a process for forming silicon wafers by ion implantation of a silicon ingot. An expansion area is formed by the implanted ions in the silicon ingot at the implant depth. The reference further discloses that hydrogen, deuterium, and helium ions can be used in the disclosed process. (See first paragraph, page 1, section (57) of the specification and claim 1). The applicants assert that the process disclosed in the cited reference supports the applicants' position that those skilled in the art had sufficient knowledge and skill as of May 1997 to practice the applicants' invention using ions other than hydrogen. In particular, the cited reference supports the applicants' position that those skilled in the art were familiar with implantation of helium ions as a means of forming bubbles in a silicon substrate.

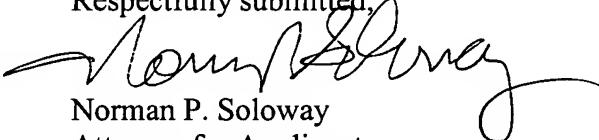
This Information Disclosure Statement is being made pursuant to the duty of disclosure imposed by law and formulated in 37 CFR 1.56(a). No representation is made that the information thus disclosed in fact constitutes prior art or that it is the closest prior art inasmuch as 37 CFR 1.56(a) relies on a materiality concept.

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The enclosed Supplemental Information Disclosure Statement is being submitted prior to issuance of the first action on the merits. Therefore, we believe there are no fees involved with this Information Disclosure Statements. In the event there are any fee deficiencies or additional fees are payable, please charge them (or credit any overpayment) to our Deposit Account No. 08-1391.

Respectfully submitted,



Norman P. Soloway
Attorney for Applicants
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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on December 30, 2004 at Tucson, Arizona.

By: 

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O 1 P INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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SC46

Docket Number (Optional)

BREV 12370 CON4

Application Number

10/784,601

Applicant(s)

ASPAR et al.

Filing Date

February 23, 2004

Group Art Unit

2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	SU 1282757	12.30.83	RUSSIA	H01L	21/265		

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.